



SOT-23 Formed SMD Package

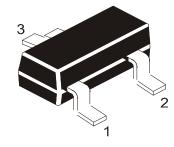
BSR20 BSR20A

SILICON P-N-P HIGH-VOLTAGE TRANSISTORS

P-N-P high-voltage small-signal transistors

Marking BSR20 = T35 BSR20A = T36

Pin configuration 1 = BASE 2 = EMITTER 3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

			BSR20	BSR20	<u>4</u>
Collector-base boltage (open emitter)	-VCB0	max.	130	160	V
Collector-emitter voltage (open base)	-V _{CE0}	max.	120	150	V
Collector current	$-I_C$	max.	600	600	mА
Total power dissipation up to $T_{amb} = 25 \ ^{\circ}C$	P _{tot}	max.	250	250	mW
Junction temperature	T_{j}	max.	150	150	° C
Collector-emitter saturation voltage	5				
$I_C = 50 mA; l_B = 5 mA$	V _{CEsat}	max.	0,5	0,5	V
D.C. current gain					
$I_C = 10 mA; V_{CE} = -5 V$	h _{FE}	min.	40	60	
		max.	180	240	

BSR20 BSR20A

RATINGS (at $T_A = 25^{\circ}C$ unless otherwise specified) Limiting values

			BSR20	BSR	20A
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	130	16	$\overline{0 V}$
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	120	15	0 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.		5	V
Collector current	$-I_C$	max.		600	mА
Total power dissipation					
up to $T_{amb} = 25 \ ^{\circ}C$	P _{tot}	max.		250	mW
Junction temperature	T_{j}	max.		150	° C
Storage temperature	Ť _{stg}		-55	to +150	° C
THERMAL RESISTANCE					

From junction to ambient	R _{th j-a}	=	500	K/W

CHARACTERISTICS

 $T_{amb} = 25$ °C unless otherwise specified

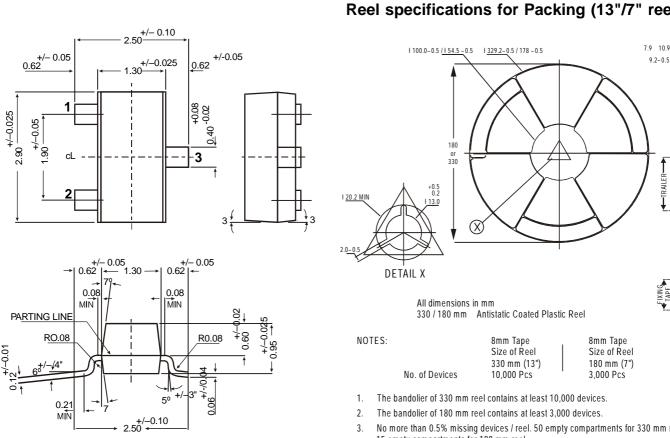
Tamb - 20 C unicss oniciwisc specificu			BSR20	BSR20A
Collector cut-off current				
$I_E = 0; -V_{CB} = 100 V$	-I _{CB0}	max.	100	nA
$I_E = 0; -V_{CB} = 120 V$	-ICB0	max.		50 nA
$I_E = 0; -V_{CB} = 100 V; T_{amb} = 100 °C$	-I _{CB0}	max.	100	μA
$I_E = 0; -V_{CB} = 120 V; T_{amb} = 100 \ C$	-I _{CB0}	max.		50 µA
Emitter cut-off current				
$I_C = 0; -V_{EB} = 4,0 V$	-I _{EB0}	max.	50	50 nA
Brealkdown voltages				
$I_C = 1.0 \ mA; \ l_B = 0$	-V(BR)CE0	min.	120	150 V
$I_C = 100 \ \mu A; \ I_E = 0$	$-V_{(BR)CB0}$	min.	130	160 V
$I_C = 0; I_E = 10 \mu A$	$-V_{(BR)EB0}$	min.	5,0	5,0 V
Saturation voltages				
$-I_C = 10 \text{ mA}; -I_B = 1,0 \text{ mA}$	-V _{CEsat}	max.	0,2	0,2 V
	-V _{BEsat}	max.	1,0	1,0 V
$-I_C = 50 \text{ mA}; -I_B = 5,0 \text{ mA}$	-V _{CEsat}	max.	0,5	0,5 V
	-V _{BEsat}	max.	1,0	1,0 V
D.C. current gain				
$I_C = 1.0 mA; -V_{CE} = 5 V$	h _{FE}	min.	30	50
$I_C = 10 \ mA; \ -V_{CE} = 5 \ V$	h _{FE}	min.	40	60
$IC = 10 \text{ mm}, -v_{CE} = 5 \text{ v}$	IIFE	max.		240
$I_{C} = 50 \ mA; -V_{CF} = 5 \ V$	hee	min.	40	50
Output capacitance at $f = 1$ MHz	h _{FE}	111111.	40	50
$I_F = 0; -V_{CB} = 10V$	Со	max.	6	6 pF
IE = 0, -VCB = 10V	00	шал.	U	0 pr

BSR20 BSR20A

			BSR20	BSR20A
Transition frequency at $f = 100 MHz$	f_T	min.	100	<i>100</i> MHz
$-I_C = 10 \text{ mA; } -V_{CE} = 10 \text{ V}$		max.	400	300 MHz
Noise figure at $R_S = 1 \ k\Omega$				
$I_C = 250 \mu A; -V_{CE} = 5 V;$				
f = 10 Hz to 15,7 kHz	F	max.	8	8 dB
Small Signal Current Gain	h _{fe}	min.	30	40
$-V_{CE} = 10V; -I_C = 1 \text{ mA}; f = 1 \text{ KHz}$		max.	200	200

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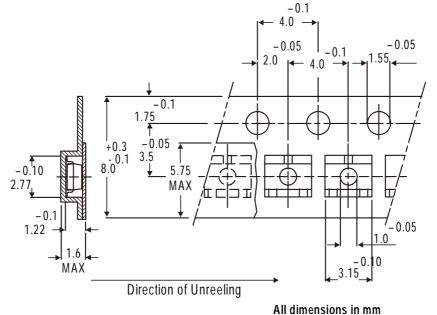


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SOT-23 Package Reel Information Reel specifications for Packing (13"/7" reels)

- No more than 0.5% missing devices / reel. 50 empty compartments for 330 mm reel. 15 empty compartments for 180 mm reel.
- 4. Three consecutive empty places might be found provided this gap is followed by 6 consecutive devices.
- 5. The carrier tape (leader) starts with at least 75 empty positions (equivalent to 330 mm). In order to fix the carrier tape a self adhesive tape of 20 to 50 mm is applied. At the end of the bandolier at least 40 empty positions (equivalent to 160 mm) are there.

Tape Specification for SOT-23 Surface Mount Device



Packing Detail

PACKAGE	STANDA	ARD PACK	INNER CARTON BOX OUTER CARTON E		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
SOT-23 T&R	3K/reel	136 gm/3K pcs	3" x 7.5" x 7.5" 9" x 9" x 9"	12.0K 51.0K	17" x 15" x 13.5" 19" x 19" x 19"	192.0K 408.0K	12 kgs 28 kgs
	10K/reel	415 gm/10K pcs	13" x 13" x 0.5"	10.0K	17" x 15" x 13.5"	300.0K	16 kgs

Customer Notes

Component Disposal Instructions

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

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